

EAST: (10669216.write line with bias structure at ends.wsp:1)

File View Edit Tools Window Help

Drafts

- BRS:
- BRS:
- BRS:
- BRS: knall
- BRS: 19 21 23
- BRS: 32with 33

Pending

Active

- L1: (0) 10/669216
- L2: (0) "APPLIED SPINTRONICS".as
- L3: (5) "TSANG, DAVID".in
- L4: (168557) (ferr?electric ferr? adj electric ferr?magnetic ferr? adj magnetic FeRr
- L5: (20720) writ\$4 adj2 line
- L6: (789915) (hard) adj2 (layer magnetization) (high adj coor\$4) bias\$4
- L7: (113203) 6 near9 end
- L9: (184) 5 and 7
- L11: (2) 8 and 4
- L8: (7) 5 same 7
- L10: (44) 8 and 4

Failed

Saved

- (1) 08/948877
- (1738) "KONINKLIJKE PHILIPS".as

Favorites

Tagged (3)

QB: USPAT:US PGPUB: EPO: JPD: DERWENT: IDM: TDC

Default operator: OR

Plurals

+highlight all hit terms initially

9 and 4

June 2004

	U	+	Investor	Document	Page	P	Title	Current	Current	Current	Retrieval	S	C	P	2	3	Image	Doc	P
1			Gagl, Dietmar	US 2004008	20040:5		Method for operating an MRAM semiconduct	711/1										US 200400	
2			Amano, Mino	US 2003012	20030:1		Magnetic memory	365/173	365/171									US 200301	
3			Hidaka, Hidet	US 2004010	20040:2		Thin film magnetic memory device with mem	365/158										US 200401	
4			Hidaka, Hidet	US 2004009	20040:4		Thin film magnetic memory device for progra	365/232										US 200400	
5			Kai, Tadashi	US 2004006	20040:2		Magnetoresistive element and magnetic me	428/468	428/208									US 200400	
6			Hidaka, Hidet	US 2004008	20040:3		Thin film magnetic memory device having da	365/200										US 200400	
7			Tanizaki, Hir	US 2003022	20031:3		Thin film magnetic memory device having du	365/158										US 200302	
8			Luo, Jih-Shiu	US 2003021	20031:1		Nonvolatile memory device utilizing spin-valv	365/158										US 200302	
9			Iwata, Yoshih	US 2003018	20030:1		Magnetic random access memory	365/200										US 200301	
10			Neel, Gary T.	US 2003013	20030:2		Fluid dose, flow-end coagulation sensor for m	73/53.0										US 200301	

Ready